

AP50N06

N-Channel Power MOSFET

描述 / Descriptions

TO-220 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a TO-220 Plastic Package.

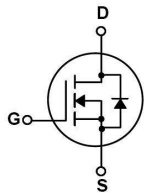
特征 / Features

$R_{DS(on)}$ 小, 门电荷低, C_{rss} 小, 开关速度快。
Low $R_{DS(on)}$, low gate charge, low C_{rss} , fast switching.

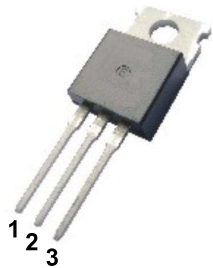
用途 / Applications

用于低压电路如：汽车电路、DC/DC 转换、便携式产品的电源高效转换。
Suited for low voltage applications such as automotive, DC/DC Converters, and high efficiency switching for power management in portable and battery operated products.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : G

PIN 2 : D

PIN 3 : S

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极限参数 / Absolute Maximum Ratings(Ta=25°C)

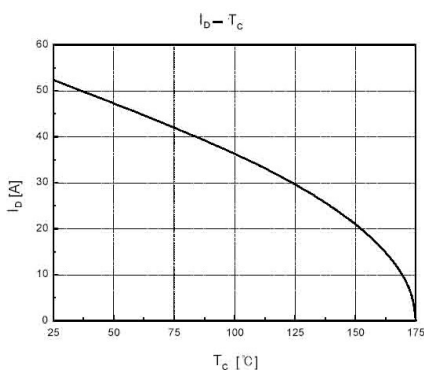
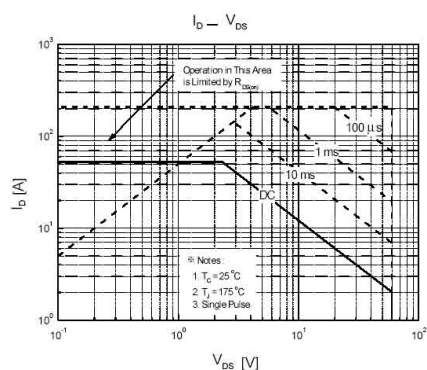
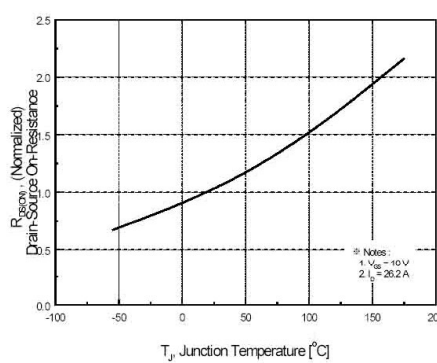
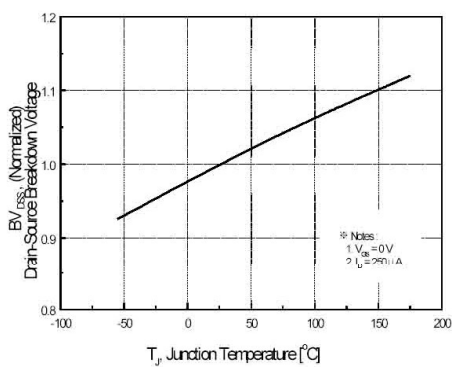
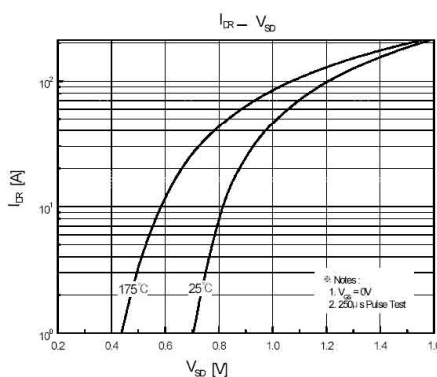
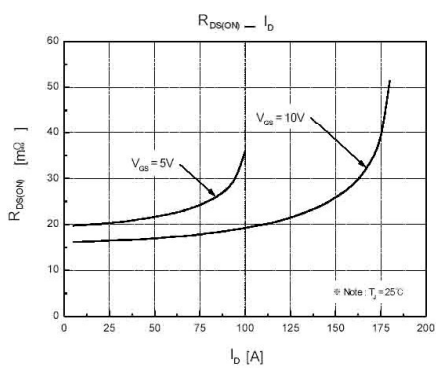
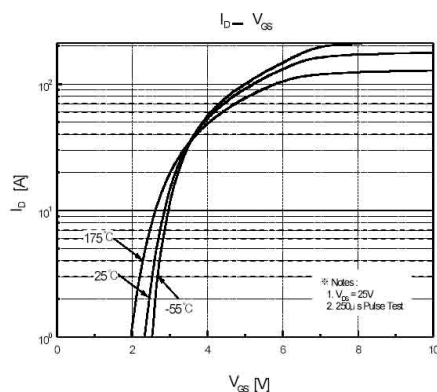
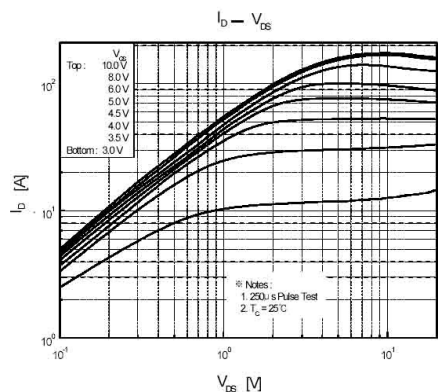
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	60	V
Drain Current	$I_D(T_c=25^\circ\text{C})$	50	A
Drain Current	$I_D(T_c=100^\circ\text{C})$	35.4	A
Drain Current - Pulsed	I_{DM}	200	A
Gate-Source Voltage	V_{GS}	± 20	V
Single Pulsed Avalanche Energy	E_{AS}	490	mJ
Avalanche Current	E_{AR}	12	mJ
Power Dissipation	$P_D(T_c=25^\circ\text{C})$	120	W
Operating Temperature Range	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55~150	$^\circ\text{C}$

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	60			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=60V$ $V_{GS}=0V$			1.0	μA
		$V_{DS}=48V$ $T_c=150^\circ\text{C}$			10	
Gate-Body Leakage Current, Forward	I_{GSS}	$V_{GS}=\pm 20V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2		4	V
Total Gate Charge	Q_g	$V_{DS}=48V$ $I_D=50A$ $V_{GS}=10V$		32	42	nC
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=25A$		0.018	0.022	Ω
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=50A$			1.5	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0\text{MHz}$		1050	1365	pF
Output Capacitance	C_{oss}			460	600	
Reverse Transfer Capacitance	C_{rss}			70	90	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=30V$ $I_D=25A$ $R_G=25\Omega$		20	50	ns
Turn-On Rise Time	t_r			100	210	
Turn-Off Delay Time	$t_{d(off)}$			80	170	
Turn-Off Fall Time	t_f			85	180	

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电参数曲线图 / Electrical Characteristic Curve

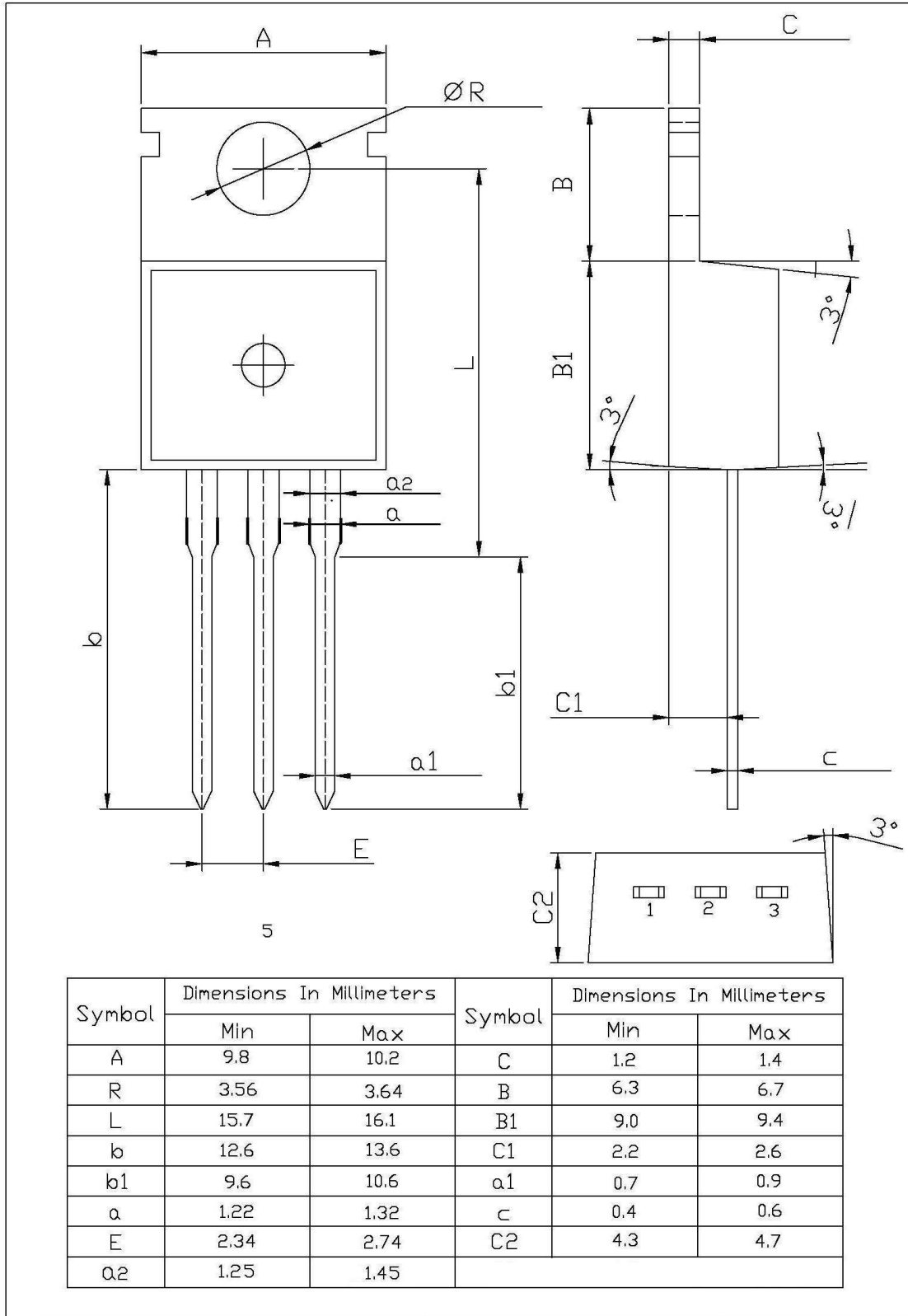


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外形尺寸图 / Package Dimensions

TO-220

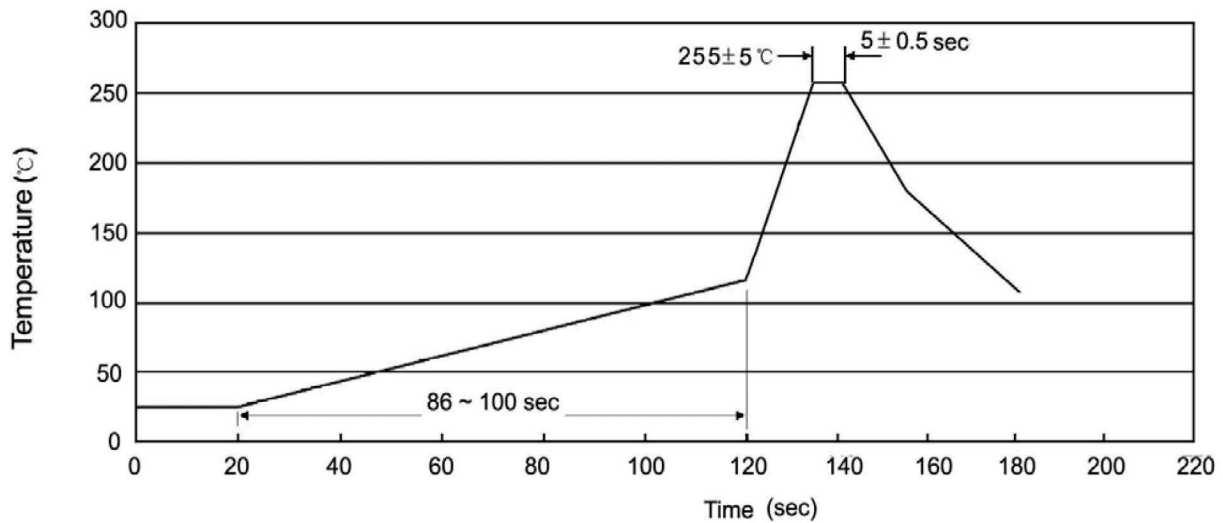
单位: mm



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波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

散件包装 / BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Bag 只/袋	Bags/Inner Box 袋/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Bag 袋	Inner Box 盒	Outer Box 箱
TO-220/F	200	10	2,000	5	10,000	135×190	237×172×102	560×245×195

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Tube 套管	Inner Box 盒	Outer Box 箱
TO-220/F	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices